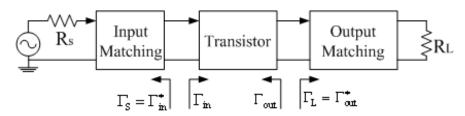
射頻或微波放大器分兩類,第一類是低雜訊放大器,另一類是最佳功率增益放大器,設計工作實際上就是要設計輸入與輸出兩匹配電路 (Matching Circuits)如下圖所示,使達到特定的匹配,前者實際上就是要設計輸入匹配電路(Matching Circuits)在最佳雜訊點;而後者兩匹配電路是要將電晶體的輸入阻抗與前級阻抗 Rs 匹配,同時輸出阻抗與外加負載阻抗 RL 匹配,達到最佳功率增益。



(A) 低雜訊放大設計 已知雜訊指數如下公式

$$F = F_{\min} + \frac{4r_n \left| \Gamma_s - \Gamma_{s, \text{opt}} \right|^2}{\left( 1 - \left| \Gamma_s \right|^2 \right) 1 + \left| \Gamma_{s, \text{opt}} \right|^2}$$

定義雜訊指數F的參數N

$$\begin{split} N_{\mathrm{i}} &\equiv \frac{\left|\Gamma_{\mathrm{s}} - \Gamma_{\mathrm{s,opt}}\right|^{2}}{\left(1 - \left|\Gamma_{\mathrm{s}}\right|^{2}\right)^{2}} \\ \therefore F_{\mathrm{i}} &= F_{\mathrm{min}} + \frac{4r_{\mathrm{n}}N_{\mathrm{i}}}{\left|1 + \Gamma_{\mathrm{s,opt}}\right|^{2}} \end{split}$$

一般最佳雜訊指數  $F_{min}$ 、  $r_n=R_n/50$ 、及  $\Gamma_{S,opt}$ 由廠商提供。任一雜訊參數 Ni 對 應一  $F_i$ ,而且滿足圓方程式

$$\begin{split} \therefore \left| \Gamma_{s} - \frac{\Gamma_{s, \text{opt}}}{\left( 1 + N_{i} \right)} \right|^{2} &= \frac{N_{i}^{2} + N_{i} \left( 1 - \left| \Gamma_{s, \text{opt}} \right|^{2} \right)}{\left( 1 + N_{i} \right)^{2}} \\ & \boxed{\square} \text{ is } = \frac{\Gamma_{s, \text{opt}}}{\left( 1 + N_{i} \right)} \\ & \boxed{\text{if }} \boxed{\square} \end{split}$$

$$\# \overline{\mathcal{A}} = \frac{\left[N_i^2 + N_i \left(1 - \left|\Gamma_{s,opt}\right|^2\right)\right]^{/2}}{\left(1 + N_i\right)}$$

低雜訊放大的設計程序是先決定了。後再帶入

$$\Gamma_{out} = S_{22} + \frac{S_{12}S_{21}\Gamma_s}{1 - S_{11}\Gamma_s} = \Gamma_L^*$$

由 $\Gamma_s$ 及 $\Gamma_L$ 就可設計輸入及輸出匹配電路。

## (B) 最佳功率增益設計

選擇電晶體最重要的兩件事情是穩定度 K>1 以及能夠提供最佳的增益 MAG。

Rollett Stability Factor K,

$$K = \frac{1 - \left| S_{11} \right|^2 - \left| S_{22} \right|^2 + \Delta^2}{2 \left| S_{12} S_{21} \right|}$$
 K> Inherent Stability

MAG = 
$$\frac{|S_{21}|}{|S_{12}|} (K - \sqrt{K^2 - 1})$$

電晶體輸入端的反射係數為

$$\Gamma_{\text{in}} = s_{11} + \frac{s_{12}s_{21}\Gamma_L}{1 - \Gamma_L s_{22}}$$

電晶體輸出端的反射係數為

$$\Gamma_{\text{out}} = s_{22} + \frac{s_{12}s_{21}\Gamma_s}{1 - \Gamma_s s_{11}}$$

在互為共軛匹配的條件下可得最佳的反射係數與S參數關係

$$\begin{split} \Gamma_{sopt} &= \frac{B_1 - \sqrt{B_1^2 - 4|C_1|^2}}{2C_1} \\ \Gamma_{Lopt} &= \frac{B_2 - \sqrt{B_2^2 - 4|C_2|^2}}{2C_2} \end{split}$$

$$B_1 &= 1 + |S_{11}|^2 - |S_{22}|^2 - |\Delta|^2 \\ B_2 &= 1 + |S_{22}|^2 - |S_{11}|^2 - |\Delta|^2 \\ C_1 &= S_{11} - S_{22}^* \Delta \\ C_2 &= S_{22} - S_{11}^* \Delta \\ \Delta &= S_{11} S_{22} - S_{12} S_{21} \end{split}$$

Available power gain GA

$$G_{A} = \frac{\text{Power Available from the Amplifier}}{\text{Power Available from the Source}}$$

$$= G_{T}|_{\Gamma_{L} = \Gamma_{out}^{*}}$$

$$= \frac{\left|S_{21}\right|^{2} \left(1 - \left|\Gamma_{s}\right|^{2}\right)}{\left(1 - \left|\Gamma_{out}\right|^{2}\right) \left|1 - S_{11}\Gamma_{s}\right|^{2}}$$

射頻放大器的增益有多種定義,其中與實際網路分析儀量測符合的是 Transducer Gain Gr

$$G_{T} = \frac{\text{Power Delivered to the Load}}{\text{Available Power from the Source}}$$
$$= \frac{\left(1 - \left|\Gamma_{L}\right|^{2}\right)\left|S_{21}\right|^{2}\left(1 - \left|\Gamma_{S}\right|^{2}\right)}{\left|1 - \Gamma_{L}S_{22}\right|^{2}\left|1 - S_{11}\Gamma_{S}\right|^{2}}$$

今已知有一個微波的電晶體 2N6680 GaAs FET 6GHz 其[S]參數及雜訊指數如下表所列:

S-Parameter	Noise Parameters
S <sub>11</sub> =0.641/-171.3°	F <sub>min</sub> =2.9dB
S <sub>12</sub> =0.057/16.3°	R <sub>n</sub> =9.42Ω
S <sub>21</sub> =2.058/28.5°	Γ <sub>S,opt</sub> =0.542/141°
S <sub>22</sub> =0.572/-95.7°	

## 請同學

- (1) 用 MATLAB 等軟體(a)建立程式計算上面所提兩種電路所需  $\Gamma$  s、  $\Gamma$  L,NF、及  $G_{\Gamma}$  (b)並繪出 NF=3、4、5dB 的等雜訊圓。
- (2) 利用微條線匹配技術設計兩匹配電路,
- (3) 利用微波軟體(ADS)驗證下表結果。

本習題結論:低雜訊放大獲得低雜訊,但付出代價是低增益及高輸入反射係數。

2N6680 GaAs FET 6GHz						
Γs (Mag/Ang)	Γ <sub>L</sub> (Mag/Ang)	NF(dB)	G <sub>T</sub> (dB)	Input SWR	Output SWR	
0.542/141	0.575/104	2.90	9.33	3.82:1	1.00:1	
0.762/177	0.718/104	4.44	11.38	1.00:1	1.00:1	

 $=\infty$  (Open Circuit)

1. 用傳輸線匹配可參考老師的書,為方便先提供下列公式供大家參考

$$Z(d) = Z_o \frac{Z_L + jZ_o \tan\beta d}{Z_o + jZ_L \tan\beta d}$$

$$(1) \text{ if } Z_L = \infty = \text{Open and } d = \lambda/8$$

$$Z(d) = Z_o \frac{JZ_o}{jZ_L} = -jZo$$

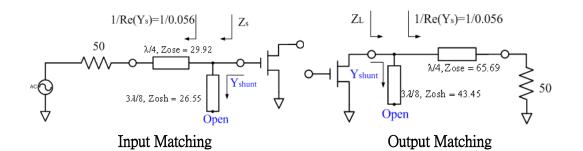
$$Z(d) = Z_o \frac{JZ_o}{jZ_L} = -jZo$$

$$Z(d) \times Z_L = Z_o^2$$

$$Z(d) \times Z_L = Z_o$$

3λ/8 Open-ended TL as Inductance

3. 參考設計



Гs (Mag/Ang)	Γ <sub>L</sub> (Mag/Ang)	NF(dB)	G <sub>T</sub> (dB)	Input SWR	Output SWR
0.614/160	0.627/106	3.14	10.55	2.28:1	1.00:1

clc;	S =
clear;	-0.6336 - 0.0970i 0.0547 + 0.0160i
Z0=50;	1.8086 + 0.9820i -0.0568 - 0.5692i
S11=0.641*exp(i*(-171.3)*pi/180);	rn =
S12=0.057*exp(i*(16.3)*pi/180);	0.1884
S21=2.058*exp(i*(28.5)*pi/180);	Tsmin =
S22=0.572*exp(i*(-95.7)*pi/180);	-0.4204 + 0.3405i
S=[S11 S12;S21 S22]	Tomin =
Fmin=2.9;Rn=9.42;	-0.1438 - 0.5566i
rn=Rn/Z0	TLmin =
	-0.1438 + 0.5566i
Tsmin=0.541*exp(i*141*pi/180)	MTL1 =
Tomin=S22+((S12*S21*Tsmin)/(1-(Tsmin*S11)))	0.5749 104.4851
TLmin=conj(Tomin)	Ga1 =
MTL1=[abs(TLmin) angle(TLmin)*180/pi]	8.5811
	Zs1 =
Ga1=(abs(S21)^2*(1-abs(Tsmin)^2))/((1-	16.5761 +15.9575i
abs(Tomin)^2)*abs(1-S11*Tsmin)^2)	Zo1 =
	20.6887 -34.3992i
Zs1=(1+Tsmin)*Z0/(1-Tsmin)	ZL1 =
Zo1=(1+Tomin)*Z0/(1-Tomin)	20.6887 +34.3992i
ZL1=(1+TLmin)*Z0/(1-TLmin)	Delta =
Delta=(S11*S22)-(S12*S21)	-0.1024 + 0.2835i
B1=1+abs(S11)^2-abs(S22)^2-abs(Delta)^2;	A =
B2=1-abs(S11)^2+abs(S22)^2-abs(Delta)^2;	0.9928 + 0.0000i 0.8254 + 0.0000i
C1=S11-conj(S22)*Delta;	-0.4781 - 0.0226i -0.0942 - 0.3796i

C2=S22-conj(S11)\*Delta; Tsmax = A=[B1 B2;C1 C2] -0.7611 + 0.0359iTLmax =  $Tsmax=(B1-sqrt(B1^2-4*(abs(C1)^2)))/(2*C1)$ -0.1731 + 0.6972i $TLmax=(B2-sqrt(B2^2-4*(abs(C2)^2)))/(2*C2)$ MTS2 = Tomax=conj(TLmax) 0.7619 177.2990 MTS2=[abs(Tsmax) angle(Tsmax)\*180/pi] MTL2 = MTL2=[abs(TLmax) angle(TLmax)\*180/pi] 0.7184 103.9397 Zs2 = Zs2=(1+Tsmax)\*Z0/(1-Tsmax)6.7593 + 1.1572iZL2=(1+TLmax)\*Z0/(1-TLmax)ZL2 =12.9934 +37.4412i F2 = F2=Fmin+(4\*rn\*abs(Tsmax-Tsmin)^2)/((1abs(Tsmax)^2)\*abs(1+Tsmin)^2) 3.7303 Ga2 = Ga2=(abs(S21)^2\*(1-abs(Tsmax)^2))/((1abs(Tomax)^2)\*abs(1-S11\*Tsmax)^2) 13.7451

